

Number of layers of MoS₂ determined using Raman Spectroscopy

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Abstract

Presentation of two methods based on Raman spectroscopy for determining the number of layers of MoS₂.

Key words

MoS₂, Molybdenum disulfide, nanomaterials analysis, Raman spectroscopy, Raman imaging

Layered low-dimensional structures

There are two types of vibrational modes in MoS₂ (as in all layered structures): vibrational modes inside layers (intralayer) and modes resulting from the movements of complete layers (interlayer). The intralayer modes are primary related to the chemical composition of a layer (or layers) and are their fingerprint; however these can be slightly influenced by the number of layers. The interlayer modes, due to the high mass of the layers, are observed at very low frequencies and their position depends on the number of layers. As a result, both types of modes can be used to determine the number of layers.



Figure 1: Optical image of the MoS₂ sample. The blue rectangle corresponds to the mapped surface.

Method 1: Analysis of fingerprint modes (intralayer)

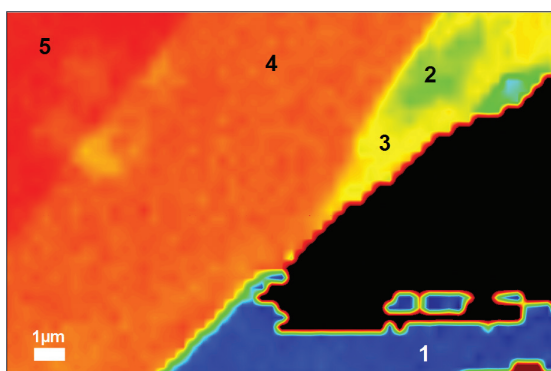


Figure 2a: A Raman map of MoS₂ with different number of single layers based on the fingerprint modes analysis.

The number of layers can be found by determining the distance between two fingerprint peaks (observed at ~383 cm⁻¹ and ~408 cm⁻¹

Method 2: Analysis of low-frequency modes (interlayer)

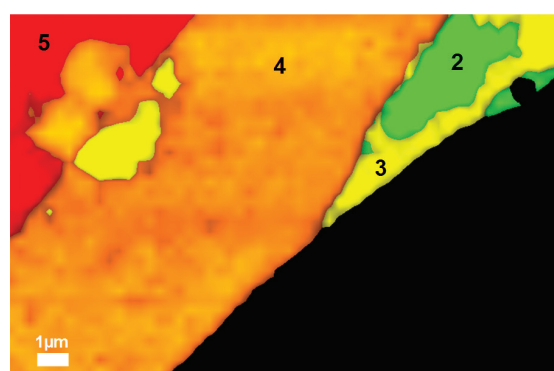


Figure 3a: A Raman map of MoS₂ with different number of single layers based on low frequency modes analysis.

The analysis is very straightforward and consists of mapping individual peaks corresponding to different number of single layers (the spectra

in bulk MoS₂ [2]). With increasing number of single layers the mode at ~383 cm⁻¹ shifts to lower frequencies and the mode at ~408 cm⁻¹ shifts to higher frequencies (figure 2b).

To obtain the image presented at the figure 2a, first, the fitting of peaks were done to find exact peak positions, then the difference between the peak positions were calculated and imaged. When the number of layers is higher than four the frequency of both peaks converge to the bulk values, which results in decreasing capacity of differentiating between the layers of different thickness.

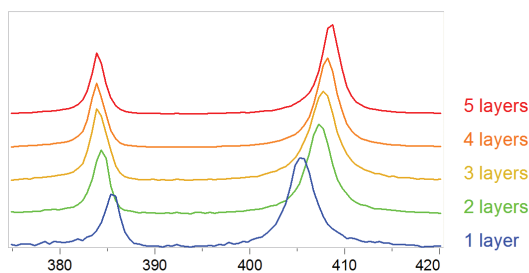


Figure 2b: Raman spectra of MoS₂ in the fingerprint region.

are shown in figure 3b). As they are relatively well resolved, a simple analysis using map cursors to follow peak intensities is sufficient; in this study CLS fitting was used for better contrast.

The interlayer modes appear below 35 cm⁻¹. In this analysis, the main shear mode was used; other peaks observed in this region correspond to secondary shear modes or to compression modes; they give additional information and allow the identification of number of layers without ambiguity. Their frequencies can be predicted taking into account the weight of a layer and shearing strength. More details can be found in refs. [1] and [3].

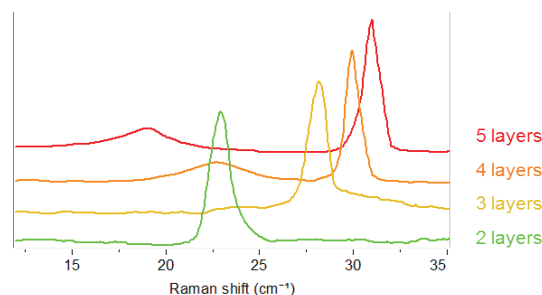


Figure 3b: Raman spectra of MoS₂ in the low frequency region

Conclusions

The two methods give complementary results and allow the determination of the number of layers. Method 2 (using low frequency modes) gives excellent contrast; however it does not show single layer regions (which is related to the nature of the modes, rising from interaction between at least two layers). Method 1 (using fingerprint modes) shows all the layers, but the contrast is poorer, particularly for higher numbers of layers. The best result can be obtained combining the two methods:

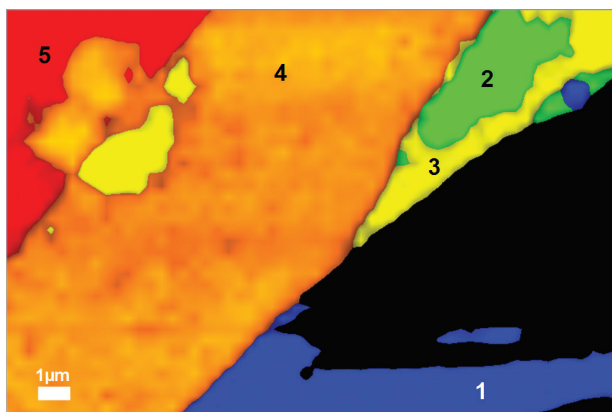


Figure 4: A combined Raman map of MoS₂ layers.

Experimental details

All the measurements (low-frequency and fingerprint) were done using ultra-low frequency ULF™ filters which allow a high throughput measurement in a full Raman range, down to <10 cm⁻¹ (<http://www.horiba.com/scientific/products/raman-spectroscopy/accessories/ultra-low-frequency-raman-module/>).

Further reading

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